

35.C10530C/D2



PATENT APPLICATION

#5
Ree
Amdd
B
10/27/99
A. Jenkins

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
KIYOFUMI SAKAGUCHI, ET AL.) Examiner: Not Yet Assigned
Application No.: 09/161,774) Group Art Unit: ~~2812~~ 2823
Filed: September 29, 1998)
For: PROCESS FOR PRODUCTION)
OF SEMICONDUCTOR)
SUBSTRATE) September 22, 1999

Assistant Commissioner for Patents
Washington, D.C. 20231

SECOND PRELIMINARY AMENDMENT

RECEIVED
SEP 23 1999
TC 2800 MAIL ROOM

Sir:

Prior to examination on the merits, please further
amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel Claims 22 - 96 without prejudice to
or disclaimer of the subject matter recited therein.

Please add new Claims 97 through 104 as follows:

97. A method for separating a semiconductor layer
from a substrate, comprising:

forming a porous layer on a surface of a
substrate by an anodic oxidization;